

Dopant Diffusion and Current-Voltage Studies on Epitaxial InP Codoped with Ru and Re*

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The following table was inadvertently omitted when this article was originally printed in the August 2001 issue of the *Journal of Electronic Materials*, Vol. 30, No. 8, pp. 972–976.

Table I. Ru and Fe Concentrations in the Samples in the Investigation

Identity	SI-Layer	Ru (cm ⁻³)	Fe (cm ⁻³)	Thickness (μm)
n(sub)-SI-n				
725D1	InP:Ru	3.9×10^{17}	—	3.5
732D2	InP:Ru,Fe	1.9×10^{17}	4.9×10^{17}	4.1
735B1	InP:Ru,Fe	2.5×10^{17}	4.3×10^{17}	4.3
p(sub)-SI-p				
725B2	InP:Ru	4.0×10^{17}	—	3.5
732A2	InP:Ru,Fe	1.9×10^{17}	4.9×10^{17}	4.2
735C1	InP:Ru,Fe	2.7×10^{17}	4.5×10^{17}	4.5

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